

SOT89 NPN SILICON POWER (SWITCHING) TRANSISTOR

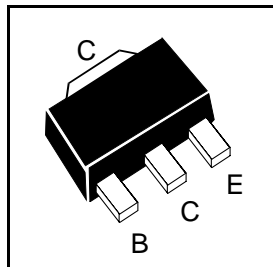
ISSUE 1 - NOVEMBER 1998

FCX688B

FEATURES

- * **2W POWER DISSIPATION**
- * 10A Peak Pulse Current
- * Excellent H_{FE} Characteristics up to 10 Amps
- * Extremely Low Saturation Voltage

Complimentary Type - FCX789A
Partmarking Detail - 688



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	12	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current **	I_{CM}	10	A
Continuous Collector Current	I_C	3	A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1 † 2 ‡	W W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

† recommended P_{tot} calculated using FR4 measuring 15x15x0.6mm

‡ Maximum power dissipation is calculated assuming that the device is mounted on FR4 substrate measuring 40x40x0.6mm and using comparable measurement methods adopted by other suppliers.

**Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle \leq 2%

Spice parameter data is available upon request for these devices

Refer to the handling instructions for soldering surface mount components.

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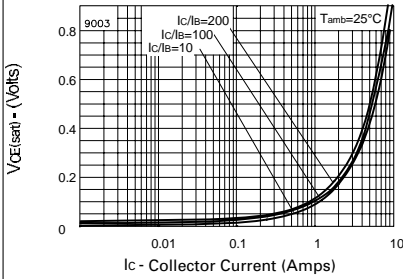
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$)

PARAMETER	SYMBOL	Min	Typ	Max	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	12			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	12			V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			0.1	μA	$V_{CB}=9\text{V}$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			40 60 180 350 400	mV mV mV mV mV	$I_C=0.1\text{A}, I_B=1\text{mA}^*$ $I_C=0.1\text{A}, I_B=0.5\text{mA}^*$ $I_C=1\text{A}, I_B=10\text{mA}^*$ $I_C=3\text{A}, I_B=10\text{mA}^*$ $I_C=4\text{A}, I_B=50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.1	V	$I_C=3\text{A}, I_B=20\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1.0	V	$I_C=3\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	500 400 100				$I_C=100\text{mA}, V_{CE}=2\text{V}^*$ $I_C=3\text{A}, V_{CE}=2\text{V}^*$ $I_C=10\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	150			MHz	$I_C=50\text{mA}, V_{CE}=5\text{V}$ $f=50\text{MHz}$
Input Capacitance	C_{ibo}		200		pF	$V_{EB}=0.5\text{V}, f=1\text{MHz}$
Output Capacitance	C_{obo}		40		pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching Times	t_{on} t_{off}		40 500		ns ns	$I_C=500\text{mA}, I_{B1}=I_{B2}=50\text{mA}$ $V_{CC}=10\text{V}$

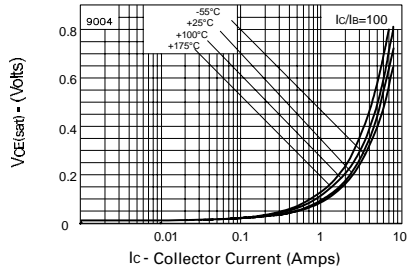
*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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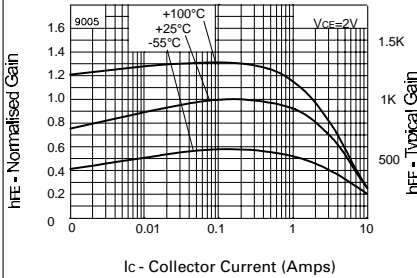
TYPICAL CHARACTERISTICS



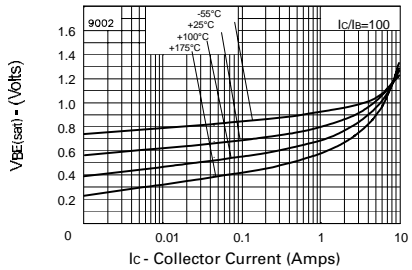
VCE(sat) v IC



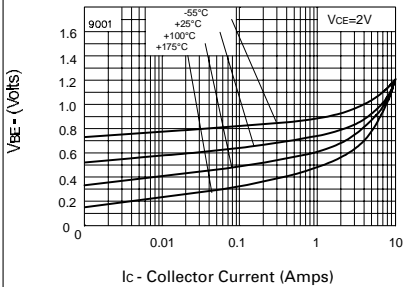
VCE(sat) v IC



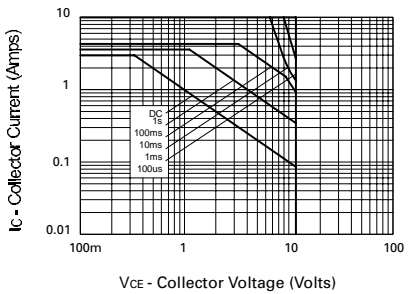
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area